

MOS FIELD EFFECT TRANSISTOR μ PA2510

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA2510, which has a heat spreader, is P-channel MOS Field Effect Transistor designed for power management applications of notebook computers.

FEATURES

- μ PA2510 has a thin surface mount package with a heat spreader. The land size is same as 8-pin TSSOP.
- Low on-state resistance

 $R_{DS(on)1}$ = 10.1 m Ω MAX. (Vgs = $-10.0\,V,\ I_D$ = $-9.0\,A)$

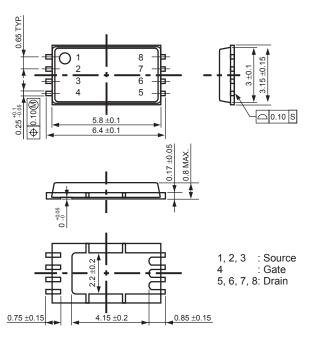
 $R_{DS(on)2} = 14.0 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = -4.5 \text{ V}, I_D = -9.0 \text{ A)}$

• Low Ciss: 3000 pF TYP. (VDS = -10.0 V, VGS = 0 V)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA2510TM	8PIN HWSON

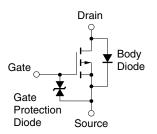
PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-30.0	V
Gate to Source Voltage (VDS = 0 V)	Vgss	∓20.0	V
Drain Current (DC) Note1	I _{D(DC)}	∓18.0	Α
Drain Current (pulse) Note2	D(pulse)	∓72.0	Α
Total Power Dissipation Note1	Рт	2.7	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note3	las	-18.0	Α
Single Avalanche Energy Note3	Eas	32.4	mJ

EQUIVALENT CIRCUIT



- **Notes 1.** Mounted on FR-4 board of 25 cm² x 1.6 mm, PW \leq 10 sec
 - **2.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - 3. Starting T_{ch} = 25°C, V_{DD} = -30 V, R_G = 25 Ω , V_{GS} = $-20.0 \rightarrow 0$ V

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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ELECTRICAL CHARACTERISTICS (TA = 25°C)

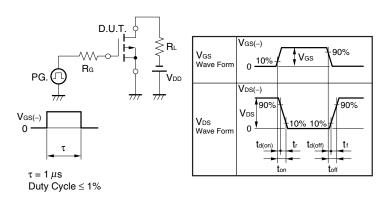
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = -30.0 V, V _{GS} = 0 V			-1.0	μΑ
Gate Leakage Current	Igss	V _{GS} = ∓20.0 V, V _{DS} = 0 V			∓10.0	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10.0 V, I _D = -1.0 mA	-1.0		-2.5	٧
Forward Transfer Admittance Note	y fs	V _{DS} = -10.0 V, I _D = -9.0 A	12			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = -10.0 V, I _D = -9.0 A		7.5	10.1	mΩ
	RDS(on)2	V _{GS} = -4.5 V, I _D = -9.0 A		9.5	14.0	mΩ
Input Capacitance	Ciss	V _{DS} = -10.0 V		3000		pF
Output Capacitance	Coss	V _{GS} = 0 V		940		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		500		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -15.0 V, I _D = -9.0 A		12		ns
Rise Time	tr	V _{GS} = -10.0 V		18		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		270		ns
Fall Time	tf			170		ns
Total Gate Charge	Q _G	V _{DD} = -24.0 V		70		nC
Gate to Source Charge	Qgs	V _{GS} = -10.0 V		8		nC
Gate to Drain Charge	Q _{GD}	I _D = -18.0 A		22		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 18.0 A, V _{GS} = 0 V		0.85		V
Reverse Recovery Time	trr	I _F = 18.0 A, V _{GS} = 0 V		80		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		68		nC

Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = -20 \rightarrow 0 \text{ V}$ V_{DD} V_{DD} V_{DD} V_{DD} V_{DD} $Starting T_{ch}$

TEST CIRCUIT 2 SWITCHING TIME

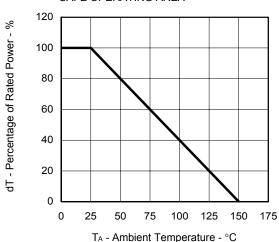


TEST CIRCUIT 3 GATE CHARGE

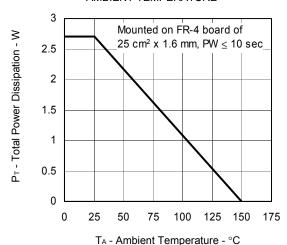
$$\begin{array}{c|c} D.U.T. \\ \hline \\ IG = -2 \text{ mA} \\ \hline \\ PG. \\ \hline \\ \end{array} \\ \begin{array}{c} SD \Omega \\ \hline \\ \end{array} \\ \begin{array}{c} VDD \\ \hline \\ \end{array}$$

TYPICAL CHARACTERISTICS (TA = 25°C)

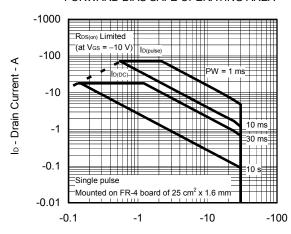
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

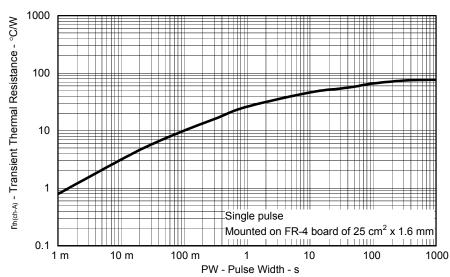


FORWARD BIAS SAFE OPERATING AREA

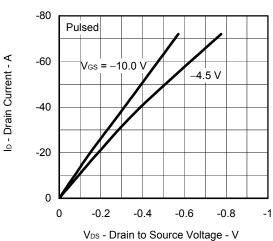


V_{DS} - Drain to Source Voltage - V

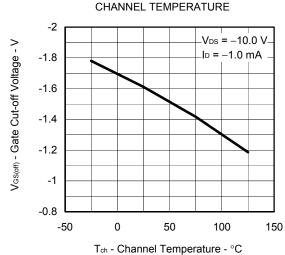
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



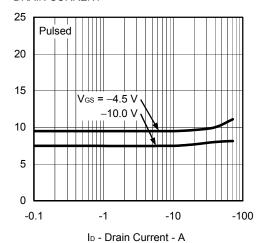
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



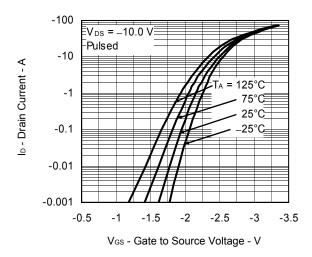
GATE CUT-OFF VOLTAGE vs.



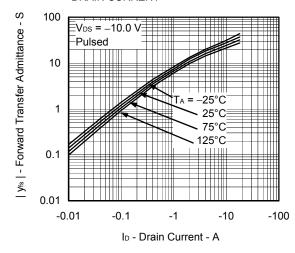
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



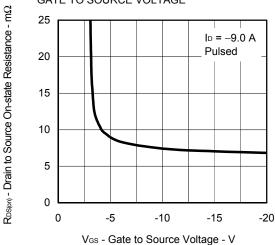
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

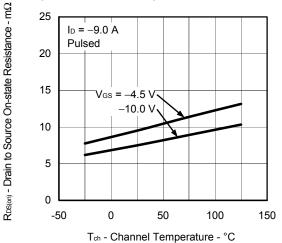


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

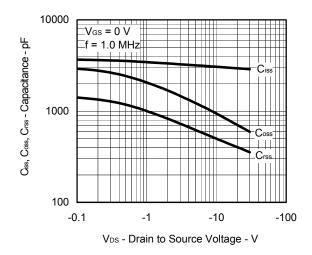


RDS(on) - Drain to Source On-state Resistance - m\Omega

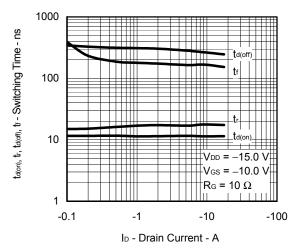
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



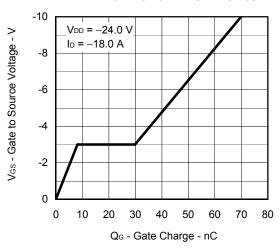
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



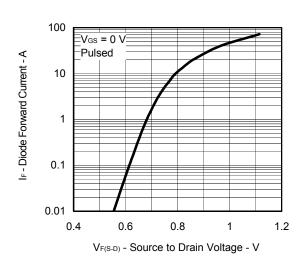
SWITCHING CHARACTERISTICS



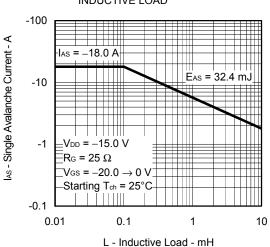
DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



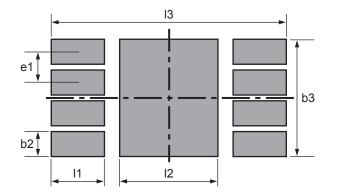
e1: 0.65 b2: 0.35 b3: 2.7 l1: 1.3

I2: 3.7 I3: 7.1

(Unit: mm)

EXAMPLE OF THE LAND PATTERN

Please optimize the land pattern in consideration of density, appearance of solder fillets, common difference, etc in an actual design.



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